

Chen-Han Chou

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Improving Interface State Density of TiN/HfO ₂ /IL Gate Stack on Si _{0.5} Ge _{0.5} by Optimization of Post Metallization Annealing and Oxygen Pressure. , 2020, , .		0
2	Comparison of the Physical and Electrical Properties of HfO ₂ /Al ₂ O ₃ /HfO ₂ /GeO _x /Ge and HfO ₂ /Al ₂ O ₃ /GeO _x /Ge Gate Stacks. Journal of Nanoscience and Nanotechnology, 2019, 19, 4529-4534.	0.9	1
3	Demonstration of HfO ₂ -Based Gate Dielectric With Low Interface State Density and Sub-nm EOT on Ge by Incorporating Ti Into Interfacial Layer. IEEE Electron Device Letters, 2019, 40, 174-176.	3.9	5
4	Incorporating Yttrium into a GeO Interfacial Layer with HfO ₂ -Based Gate Stack on Ge. ECS Journal of Solid State Science and Technology, 2018, 7, N15-N19.	1.8	6
5	Phase-separation phenomenon of NiGePt alloy on n-Ge by microwave annealing. Journal of Alloys and Compounds, 2018, 743, 262-267.	5.5	2
6	First Experimental Demonstration and Mechanism of Abnormal Palladium Diffusion Induced by Excess Interstitial Ge. IEEE Electron Device Letters, 2018, 39, 1632-1635.	3.9	0
7	Integration of microwave-annealed oxidation on germanium metal-oxide-semiconductor devices. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 051204.	1.2	1
8	Experimental Realization of Thermal Stability Enhancement of Nickel Germanide Alloy by Using TiN Metal Capping. IEEE Transactions on Electron Devices, 2017, 64, 2314-2320.	3.0	8
9	High performance Ge Schottky PMOSFETs with ternary-phase alloy. , 2016, , .		0
10	Integration of hetero-structure body-tied Ge FinFET using retrograde-well implantation. , 2016, , .		1
11	3D-TCAD simulation study of the contact all around T-FinFET structure for 10nm metal-oxide-semiconductor field-effect transistor. , 2016, , .		3
12	Experimental Realization of a Ternary-Phase Alloy Through Microwave-Activated Annealing for Ge Schottky pMOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 2714-2721.	3.0	4
13	Improving Thermal Stability and Interface State Density of High- κ Stacks by Incorporating Hf into an Interfacial Layer on p-Germanium. IEEE Electron Device Letters, 2016, 37, 1379-1382.	3.9	7
14	Low-Leakage Tetragonal ZrO ₂ (EOT \approx 1 nm) With <i>In Situ</i> Plasma Interfacial Passivation on Germanium. IEEE Electron Device Letters, 2016, 37, 138-141.	3.9	13
15	Fabricating a n+-Ge contact with ultralow specific contact resistivity by introducing a PtGe alloy as a contact metal. Applied Physics Letters, 2015, 107, 113503.	3.3	5